

A3 cut  
2. (Amended) The piezoelectric device of claim 1, wherein said porous crystalline material is selected from the group consisting of porous silicon, and, other material, with conductive channels and isolating channels such as spaces.

Please cancel claims 4 - 28.

Please add new independent claim 29 as follows:

Sub C5  
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29. (New) A method of piezoelectrically inducing strain in an element, the method comprising the steps of attaching to the element, or integrally forming with the element, an additional element of porous crystalline material being in electrical contact solely with at least one electrode, such that subjecting said additional element to an electric potential via said at least one electrode results in a strain induced by said additional element on the element.

Please add new dependent claim 30 as follows:

30. (New) The method of claim 29, wherein said porous crystalline material is selected from the group consisting of porous silicon, and, other material, with conductive channels and isolating channels such as spaces.

Please add new dependent claim 31 as follows:

31. (New) The method of claim 29, wherein the element is made of crystal material.